X3G-OH047; X3T-OH047; X3G-OH048; X3T-OH048

Magnetic field sensor

Rev. 1 — 4 April 2011

Product specification

1. Product profile

1.1 General description

The X3G-OH047, X3G-OH048, X3T-OH047 and X3T-OH048 are sensitive magnetic field sensors, employing the magneto-resistive effect of thin film permalloy. The sensors contain two parallel supplied Wheatstone bridges at a relative angle of 45° to each other.

A rotating magnetic field in the surface parallel to the chip (x-y plane) will deliver two independent sinusoidal output signals, one following a $\cos(2\alpha)$ and the other following a $\sin(2\alpha)$ function, α being the angle between sensor and field direction (see <u>Figure 5</u> and Figure 6).

The X3G-OH047, X3G-OH048, X3T-OH047 and X3T-OH048 are suited for high precision angle measurement applications under low field conditions (saturation field strength 25 kA/m).

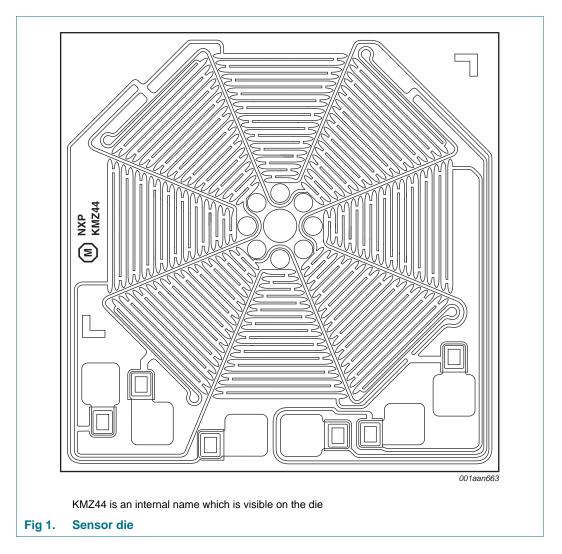
The sensors can be operated at any frequency between DC and 1 MHz.

All type numbers shown in this data sheet are valid for a single-die (single sensor). The double-die has two magnetic field sensors with electrical and magnetic parameters which fulfill the specified single-die values and do not correlate to each other.

Table 1. Product overview

Type number	Sensor	Packing
X3G-OH047	double-die	sawn wafer; on foil
X3G-OH048	single-die	sawn wafer; on foil
X3T-OH047	double-die	taped on reel
X3T-OH048	single-die	taped on reel





1.2 Features and benefits

- Accurate and reliable angle measurement
- Mechanical robustness, contactless principle
- Wear-free operation
- Accuracy independent of mechanical tolerances
- Extended temperature range

1.3 Applications

- Steering angle and torsion
- Headlight adjustment
- Motor positioning

- Window wipers
- Fuel level
- Mirror positioning

1.4 Quick reference data

Table 2. Quick reference data

 T_{amb} = 25 °C; H_{ext} = 25 kA/m; V_{CC} = 5 V; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CC}	supply voltage			-	5	9	V
V_{M}	peak voltage	see Figure 3	[1][2]	60	67	75	mV
V _{offset}	offset voltage	per supply voltage; see <u>Figure 3</u>	[1]	-2	-	+2	mV/V
TC _{V(offset)}	offset voltage temperature coefficient	per supply voltage; T _{amb} = -40 °C to +150 °C; see <u>Figure 3</u>	[1][3]	-2	-	+2	(μV/V)/K
R _{bridge}	bridge resistance		[1][4]	2.7	3.2	3.7	kΩ

- [1] Applicable for bridge 1 and bridge 2.
- [2] $V_M = |V_{O(max)} V_{offset}|$. Periodicity of V_M : $sin(2\alpha)$ and $cos(2\alpha)$, respectively.

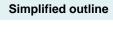
$$[3] \quad TC_{V(offset)} = \frac{V_{offset}(at\ 150\ ^{\circ}C) - V_{offset}(at\ -40\ ^{\circ}C)}{150\ ^{\circ}C - (-40\ ^{\circ}C)}$$

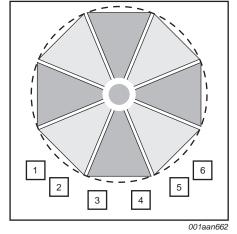
[4] Bridge resistance between pad 5 to pad 1 and pad 4 to pad 2.

2. Pinning information

Table 3. Pinning

Pad	Symbol	Description
1	ON1	output voltage bridge 1
2	ON2	output voltage bridge 2
3	GND	common ground
4	OP2	output voltage bridge 2
5	OP1	output voltage bridge 1
6	V_{CC}	common bridge supply voltage



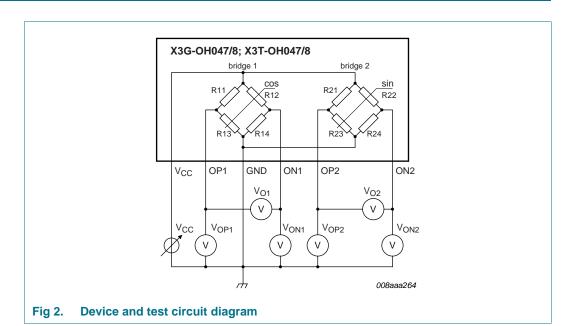


3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
X3G-OH047	bare die	double-die; sawn wafer; on foil	OL-X3G-OH047		
X3G-OH048	bare die	single-die; sawn wafer; on foil	OL-X3G-OH048		
X3T-OH047	bare die	double-die; taped on reel	OL-X3T-OH047		
X3T-OH048	bare die	single-die; taped on reel	OL-X3T-OH048		

4. Circuit diagram



Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-	9	V
H _{ext}	external magnetic field strength		<u>[1]</u> 25	-	kA/m
T _{amb}	ambient temperature		-40	+150	°C

^[1] Minimum stimulating magnetic field parallel to the chip surface (x-y plane) to achieve specified angular accuracy.

6. Characteristics

Table 6. Characteristics

 $T_{amb} = 25$ °C; $H_{ext} = 25$ kA/m^[1]; $V_{CC} = 5$ V; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CC}	supply voltage			-	5	9	V
V_{M}	peak voltage	see Figure 3	[2][3]	60	67	75	mV
TC_{VM}	peak voltage temperature coefficient	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +150 ^{\circ}\text{C}$	[2][4]	-0.30	-0.36	-0.42	%/K
R _{bridge}	bridge resistance		[2][5]	2.7	3.2	3.7	kΩ
TC _{R(bridge)}	bridge resistance temperature coefficient	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +150 ^{\circ}\text{C}$	[2][6]	0.24	0.27	0.29	%/K
V _{offset}	offset voltage	per supply voltage; see <u>Figure 3</u>	[2]	-2	-	+2	mV/V
$TC_{V(offset)}$	offset voltage temperature coefficient	per supply voltage; $T_{amb} = -40 ^{\circ}\text{C} \text{ to } +150 ^{\circ}\text{C};$ see Figure 3	[2][7]	-2	-	+2	(μV/V)/K
V _{o(hys)}	hysteresis output voltage	see Figure 4	[2][8]	0	0.05	0.18	%FS
ω	angular velocity			0	-	1	MHz
k	amplitude synchronism		<u>[9]</u>	98.9	100	101.1	%
TC _k	amplitude synchronism temperature coefficient	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +150 ^{\circ}\text{C}$	[10]	-0.01	0	+0.01	%/K
Δα	angular inaccuracy		[11]	0	0.05	0.1	deg

- [1] Minimum stimulating magnetic field parallel to the chip surface (x-y plane) to achieve angular inaccuracy.
- [2] Applicable for bridge 1 and bridge 2.
- [3] $V_M = |V_{O(max)} V_{offset}|$. Periodicity of V_M : $sin(2\alpha)$ and $cos(2\alpha)$, respectively.

$$[4] \quad TC_{VM} = \frac{V_M(at\ 150\ ^{\circ}C) - V_M(at\ -40\ ^{\circ}C)}{V_M(at\ 25\ ^{\circ}C) \times (150\ ^{\circ}C - (-40\ ^{\circ}C))}$$

[5] Bridge resistance between pad 5 to pad 1 and pad 4 to pad 2.

$$[6] \quad TC_{R(bridge)} = \frac{R_{bridge}(at\ 150\ ^{\circ}C) - R_{bridge}(at\ -40\ ^{\circ}C)}{R_{bridge}(at\ 25\ ^{\circ}C) \times (150\ ^{\circ}C - (-40\ ^{\circ}C))}$$

$$[7] \quad TC_{V(offset)} = \frac{V_{offset}(at\ 150\ ^{\circ}C) - V_{offset}(at\ -40\ ^{\circ}C)}{150\ ^{\circ}C - (-40\ ^{\circ}C)}$$

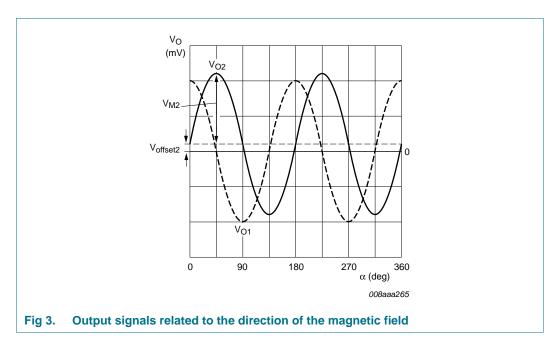
$$\begin{split} [8] \quad V_{o(hys)1} &= \left| \frac{V_{OI}(67.5^{\circ})135^{\circ} \rightarrow 45^{\circ} - V_{OI}(67.5^{\circ})45^{\circ} \rightarrow 135^{\circ}}{2 \times V_{M1}} \right| \\ V_{o(hys)2} &= \left| \frac{V_{O2}(22.5^{\circ})90^{\circ} \rightarrow 0^{\circ} - V_{O2}(22.5^{\circ})0^{\circ} \rightarrow 90^{\circ}}{2 \times V_{M2}} \right| \end{aligned}$$

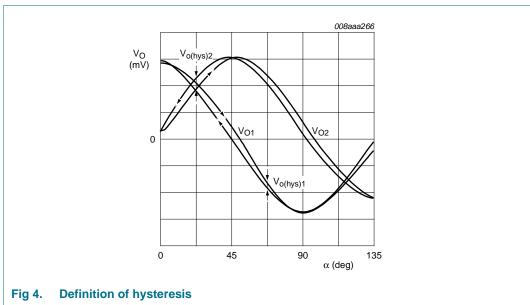
$$[9] \quad k = \frac{V_{M1}}{V_{M2}}$$

[10]
$$TC_k = \frac{k(at\ 150\ ^{\circ}C) - k(at\ -40\ ^{\circ}C)}{k(at\ 25\ ^{\circ}C) \times (150\ ^{\circ}C - (-40\ ^{\circ}C))}$$

[11] $\Delta \alpha = \left| \alpha_{\text{real}} - \alpha_{\text{meas}} \right|$; $V_{\text{offset}} = 0$ V; inaccuracy of angular measurement due to deviations from ideal sinusoidal characteristics, calculated from the third and fifth harmonics of the spectrum V_{O} .

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7. Bare die outline

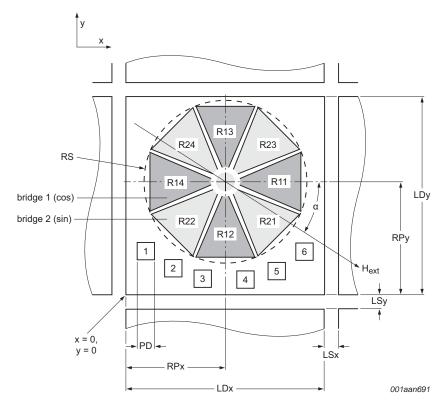


Fig 5. Bare die outline (single die)

Table 7. Mechanical dimensions for Figure 5

Symbol	Parameter	X	У	Radius/diameter	Unit
LD	die size	1150	1150	-	μm
LS	sawing lane width	60	60	-	μm
RP	reading point position	575	642	-	μm
RS	sensitive area radius	-	-	480	μm
PD	pad diameter	-	-	110	μm
1	position pad 1	108	230	-	μm
2	position pad 2	243	125	-	μm
3	position pad 3	489	95	-	μm
4	position pad 4	632	95	-	μm
5	position pad 5	900	125	-	μm
6	position pad 6	1032	200	-	μm

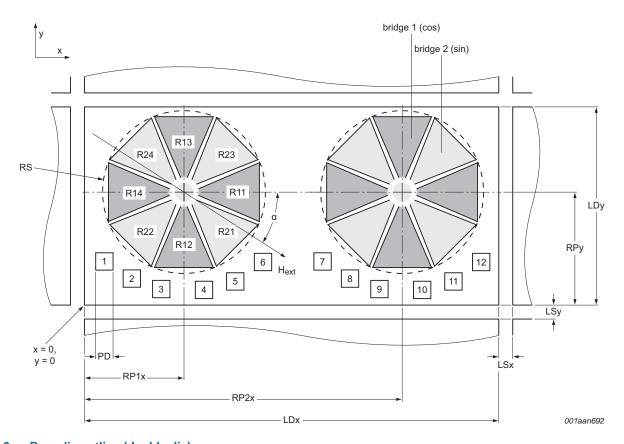


Fig 6. Bare die outline (double die)

Table 8. Mechanical dimensions for Figure 6

Symbol	Parameter	х	у	Radius/diameter	Unit
LD	die size	2360	1150		μ m
LS	sawing lane width	60	60		μ m
RP1	reading point position 1	575	642		μm
RP2	reading point position 2	1785	642		μm
RS	sensitive area radius	-	-	480	μ m
PD	pad diameter	-	-	110	μm
1	position pad 1	108	230		μm
2	position pad 2	243	125		μm
3	position pad 3	489	95		μm
4	position pad 4	632	95		μm
5	position pad 5	900	125		μm
6	position pad 6	1032	200		μ m
7	position pad 7	1318	230		μ m
8	position pad 8	1453	125		μ m
9	position pad 9	1699	95		μ m

 Table 8.
 Mechanical dimensions for Figure 6 ...continued

Symbol	Parameter	х	у	Radius/diameter	Unit
10	position pad 10	1842	95		μm
11	position pad 11	2110	125		μm
12	position pad 12	2242	200		μ m

Table 9. Wafer dimensions

Symbol	Parameter	Value	Unit
WD	wafer diameter	150	mm
WT	wafer thickness	380 ± 15	μ m

8. Packing information

8.1 Tape construction for X3G-OH047 and X3G-OH048

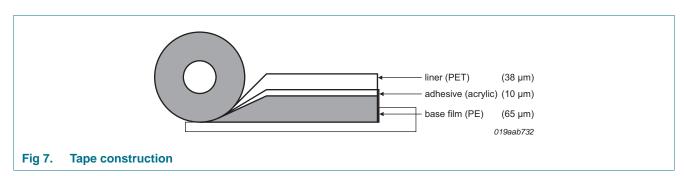
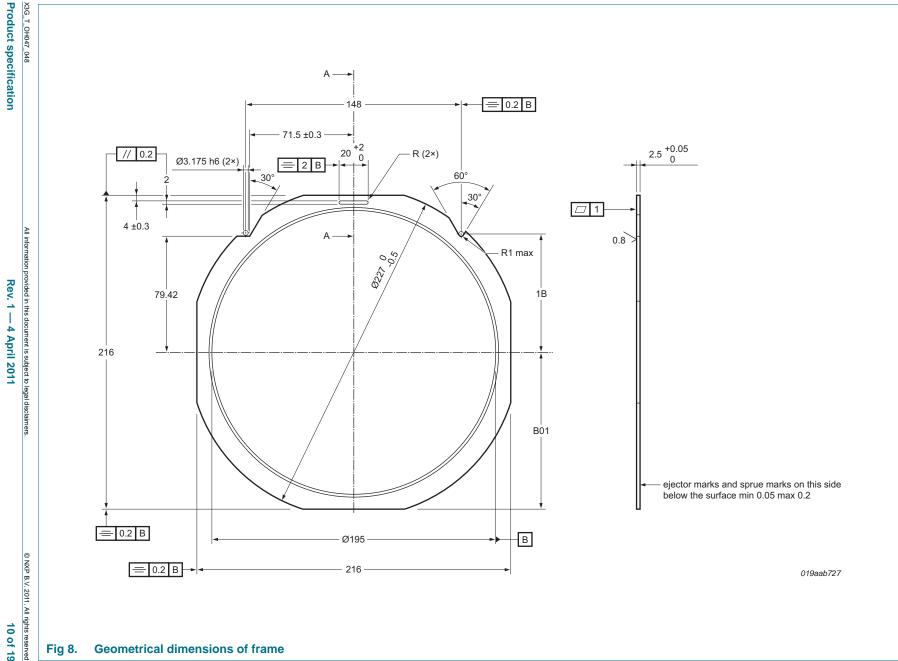
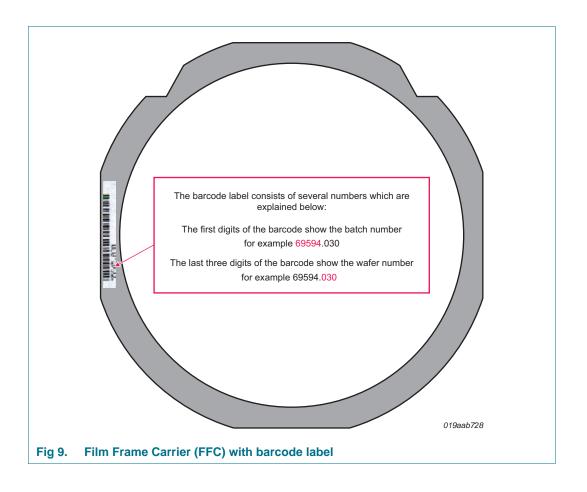


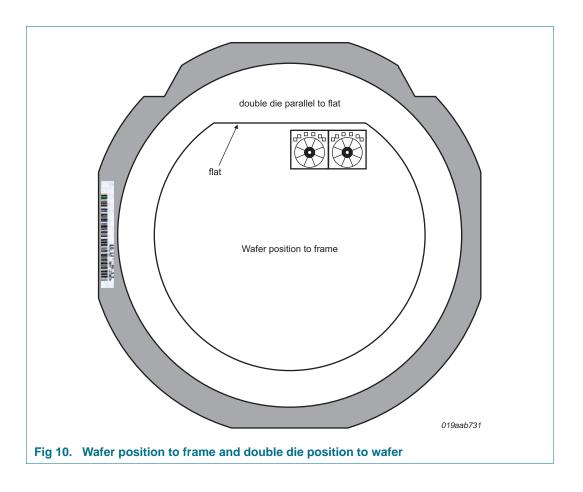
Table 10. Material composition

Parameter	Content	Typical value	Unit
Total thickness	-	75	μ m
Adhesion	-	55 / 20	g/mm
Ionic impurity	Na+	0.027	μg/ml
	K+	< 0.004	μg/ml
	CI	0.045	μg/ml





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8.2 Carrier tape for X3T-OH047 and X3T-OH048

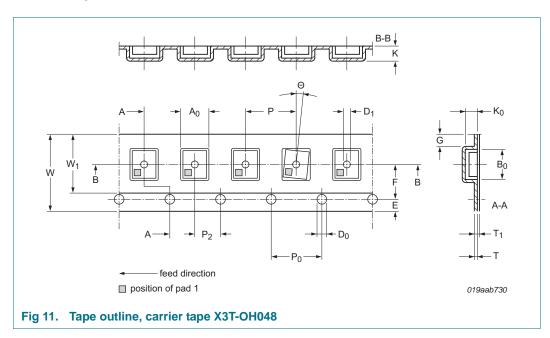


Table 11. Dimensions for Figure 11 "Tape outline, carrier tape X3T-OH048"

Item	Symbol	Specification		
		Dimension [mm]	Tolerance	
Overall dimensions				
Tape width	W	8	±0.1	
Thickness	K	≤ 1.2	-	
Distance	G	≥ 0.75	-	
Sprocket holes				
Diameter	D_0	1.5	±0.1	
Distance	E	1.75	±0.1	
Pitch[1]	P ₀	4	±0.1	
Distance between center lines				
Length direction	P ₂	2	±0.05	
Width direction	F	3.5	±0.05	
Compartments				
Length	A ₀	1.4	±0.05	
Width	B ₀	1.4	±0.05	
Depth	K ₀	0.8	±0.05	
Hole diameter	D ₁	0.5	±0.1	
Pitch	Р	4	±0.1	
Device				
Outline	X3T-OH048			
Rotation	Θ	≤ 20°	-	
Carrier tape antistatic				
Film thickness ^[2]	Т	0.25	±0.07	

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Table 11. Dimensions for Figure 11 "Tape outline, carrier tape X3T-OH048" ...continued

Item	Symbol	Specification	
		Dimension [mm]	Tolerance
Cover tape	·		
Width	W_1	≤ 5.75	-
Film thickness	T ₁	≤ 0.1	-
Bending radius			
In winding direction	R	≥ 30	-

- [1] Cumulate pitch error ± 0.2 over 10 pitch.
- [2] Carbon loaded polystyrene 100 % recyclable.

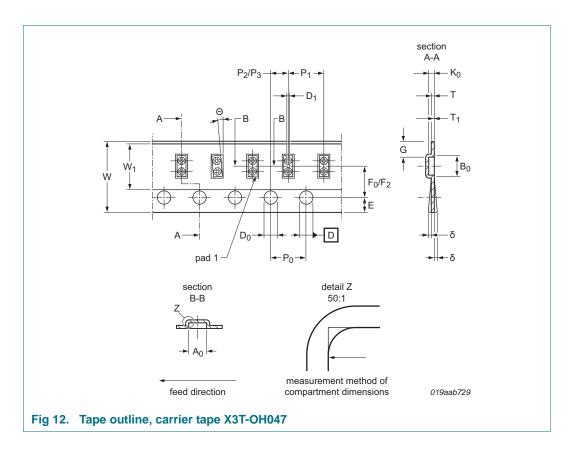


Table 12. Dimensions for Figure 12 "Tape outline, carrier tape X3T-OH047"

Item	Symbol	Specification	
		Dimension [mm]	Tolerance
Overall dimensions			
Tape width	W	8	±0.1
Distance	G	≥ 0.75	-
Sprocket holes			
Diameter	D_0	1.5	±0.1
Distance	E	1.75	±0.1
Pitch[1]	P ₀	4	±0.1

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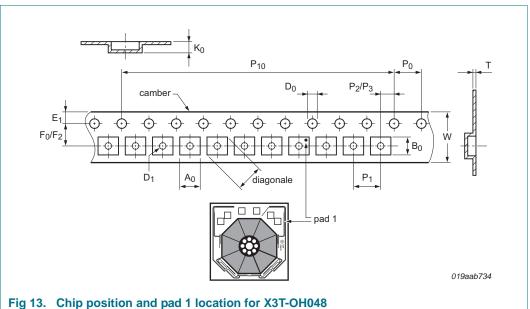
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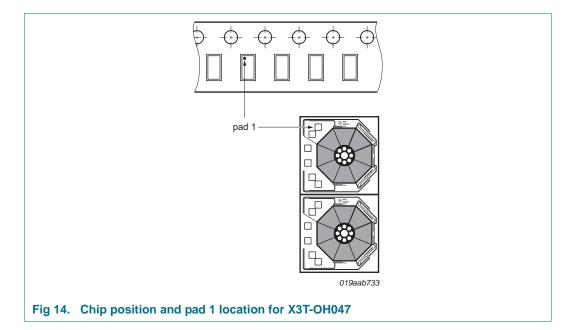
Table 12. Dimensions for Figure 12 "Tape outline, carrier tape X3T-OH047" ...continued

Item	Symbol	Specification	
		Dimension [mm]	Tolerance
Distance between center line	es		
Sprocket hole / cavity center	P_2	2	±0.05
Sprocket hole / cavity hole	P ₃	2	±0.05
Sprocket hole / cavity center	F ₀	3.5	±0.05
Sprocket hole / cavity hole	F ₂	3.5	±0.05
Compartments			
Length	A_0	1.4	±0.05
Width overall	B ₀	2.7	±0.05
Depth	K_0	0.5	±0.05
Hole diameter	D ₁	0.5	±0.1
Pitch	P ₁	4	±0.1
Device			
Outline	X3T-OH047		
Rotation	Θ	≤ 15°	-
Carrier tape antistatic			
Film thickness[2]	T	0.25	±0.07
Bend	δ	≤ 0.3	-
Cover tape			
Width	W_1	5.3	±0.1
Film thickness	T ₁	0.05	±0.01
Bending radius			
In winding direction	R	≥ 30	-

^[1] Cumulate pitch error ± 0.2 over 10 pitch.

^[2] Carbon loaded polystyrene 100 % recyclable.





Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
X3G_T_OH047_048 v.1	20110404	Product specification	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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